

L Number	Hits	Search Text	DB	Time stamp
-	139321	body near3 contact\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 14:00
-	886566	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 11:00
-	103991	parasiti\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 13:59
-	476166	sti or isolating or isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 11:02
-	44573	field adj3 (oxide or insulat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 11:03
-	369527	separat\$4 near4 (element or device or transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 11:06
-	836589	(sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 13:59
-	451	(body near3 contact\$4) same gate same ((sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 11:07
-	193	((body near3 contact\$4) same gate same ((sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor)))) and parasiti\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 13:56
-	48279	(t or h) with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 13:57
-	40618	soi or (si or silicon) adj2 insulat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/21 10:40
-	836589	(sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 13:59
-	103991	parasiti\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 14:00
-	139321	body near3 contact\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 14:00

-	116	((t or h) with gate) and (soi or (si or silicon) adj2 insulat\$4) and ((sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor)) ) and parasiti\$6 and (body near3 contact\$4 )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 14:55
-	62047	bodytie or body adj2 tie or substrate adj3 (tie or contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 14:56
-	3793	(soi or (si or silicon) adj2 insulat\$4) and (bodytie or body adj2 tie or substrate adj3 (tie or contact))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 14:57
-	2400	((soi or (si or silicon) adj2 insulat\$4) and (bodytie or body adj2 tie or substrate adj3 (tie or contact))) and ((sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor)) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 14:57
-	807	((soi or (si or silicon) adj2 insulat\$4) and (bodytie or body adj2 tie or substrate adj3 (tie or contact))) and ((sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor)) ) and parasiti\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 14:58
-	133	((soi or (si or silicon) adj2 insulat\$4) and (bodytie or body adj2 tie or substrate adj3 (tie or contact))) and ((sti or isolating or isolation) or (field adj3 (oxide or insulat\$5)) or (separat\$4 near4 (element or device or transistor)) ) and parasiti\$6 ) and ((t or h) with gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 14:59
-	1782	438/151.ccls. or 438/221.ccls. or 438/296.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 17:31
-	521029	parasitic\$4 or kink or float\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 17:31
-	626	(438/151.ccls. or 438/221.ccls. or 438/296.ccls.) and (parasitic\$4 or kink or float\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/20 17:32